



# TS13002A

## High Voltage NPN Transistor

TO-92



Pin assignment:  
 1. Emitter  
 2. Collector  
 3. Base

**BV<sub>CEO</sub> = 400V**  
**BV<sub>CBO</sub> = 700V**  
**I<sub>c</sub> = 0.3A**  
**V<sub>CE(SAT)</sub>, = 1.5V @ I<sub>c</sub> / I<sub>b</sub> = 200mA / 20mA**

**Features**

- ◊ High voltage.
- ◊ High speed switching

**Structure**

- ◊ Silicon triple diffused type.
- ◊ NPN silicon transistor

**Ordering Information**

Part No.	Packing	Package
TS13002ACT B0	Bulk	TO-92
TS13002ACT A3	AMMO pack	TO-92

**Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V <sub>CBO</sub>	700V	V
Collector-Emitter Voltage	V <sub>CEO</sub>	400V	V
Emitter-Base Voltage	V <sub>EBO</sub>	9	V
Collector Current	DC	0.3	A
	Pulse	0.5	
Collector Power Dissipation	P <sub>D</sub>	0.6	W
Operating Junction Temperature	T <sub>J</sub>	+150	°C
Operating Junction and Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

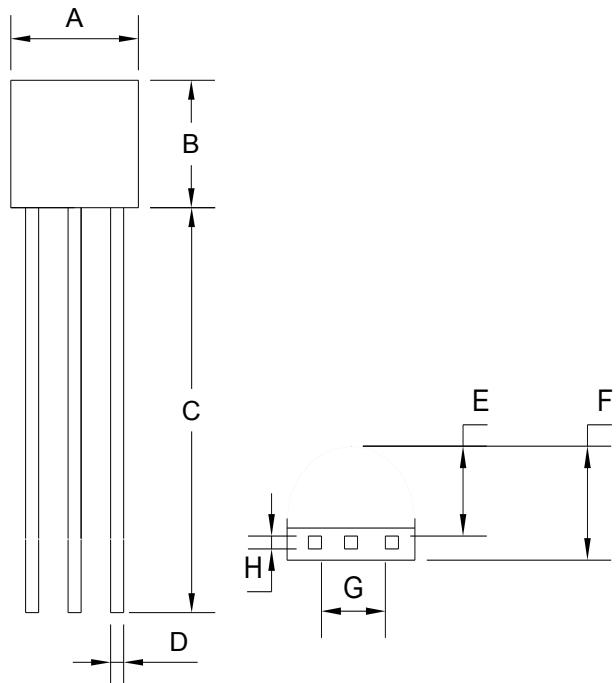
**Electrical Characteristics**

Ta = 25 °C unless otherwise noted

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Collector-Base Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	BV <sub>CBO</sub>	700	--	--	V
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>E</sub> = 0	BV <sub>CEO</sub>	400	--	--	V
Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	BV <sub>EBO</sub>	9	--	--	V
Collector Cutoff Current	V <sub>CB</sub> = 700V, I <sub>E</sub> = 0	I <sub>CBO</sub>	--	--	10	uA
Emitter Cutoff Current	V <sub>EB</sub> = 7V, I <sub>C</sub> = 0	I <sub>EBO</sub>	--	--	10	uA
Collector-Emitter Saturation Voltage	I <sub>C</sub> / I <sub>B</sub> = 200mA / 20mA	V <sub>CE(SAT)1</sub>	--	--	1.5	V
	I <sub>C</sub> / I <sub>B</sub> = 100mA / 10mA	V <sub>CE(SAT)2</sub>	--	--	1.0	
DC Current Gain	V <sub>CE</sub> = 10V, I <sub>C</sub> = 10uA	h <sub>FE1</sub>	15	--	40	
	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA	h <sub>FE2</sub>	25	--	40	
	V <sub>CE</sub> = 10V, I <sub>C</sub> = 280mA	h <sub>FE3</sub>	12	--	30	
Frequency	V <sub>CE</sub> = 10V, I <sub>C</sub> = 0.1A	f <sub>T</sub>	4	--	--	MHz
Output Capacitance	V <sub>CB</sub> = 10V, f = 0.1MHz	C <sub>ob</sub>	--	21	--	pF
Turn On Time	V <sub>CC</sub> = 125V, I <sub>C</sub> = 100mA, I <sub>B1</sub> = I <sub>B2</sub> = 20mA, R <sub>L</sub> = 125ohm	t <sub>ON</sub>	--	1.1	--	μS
Storage Time		t <sub>STG</sub>	--	--	4	μS
Fall Time		t <sub>f</sub>	--	--	0.7	μS

Note : pulse test: pulse width &lt;=5mS, duty cycle &lt;=10%

## TO-92 Mechanical Drawing



TO-92 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	14.30(typ)		0.563(typ)	
D	0.43	0.49	0.017	0.019
E	2.19	2.81	0.086	0.111
F	3.30	3.70	0.130	0.146
G	2.42	2.66	0.095	0.105
H	0.37	0.43	0.015	0.017